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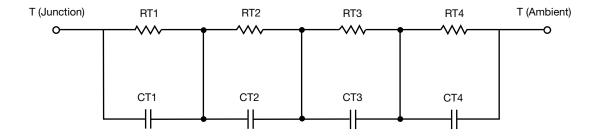
# **R-C Thermal Model Parameters**

### **DESCRIPTION**

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. R-C values for the electrical circuit in the Foster/tank and Cauer/filter configurations are included. When implemented in P-SPICE, these values have matching characteristic curves to the single-pulse transient thermal impedance curves for the MOSFET.

These RC values can be used in the P-SPICE simulation to evaluate the thermal behavior of the MOSFET junction temperature under a defined power profile. These techniques are described in application note AN609, "Thermal Simulation of Power MOSFETs on the P-SPICE Platform".

#### R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK	C VALUES FOR TANK CONFIGURATION					
	THERMAL RESISTANCE (°C/W)					
Junction to	Ambient	Case	Foot			
RT1	N/A	671.3140m	N/A			
RT2	N/A	959.8287m	N/A			
RT3	N/A	897.7798m	N/A			
RT4	N/A	467.8603m	N/A			
	THERMAL CAPAC	CITANCE (Joules/°C)				
Junction to	Ambient	Case	Foot			
CT1	N/A	340.8206m	N/A			
CT2	N/A	13.3949m	N/A			
CT3	N/A	838.9427u	N/A			
CT4	N/A	15.9540m	N/A			

#### Note

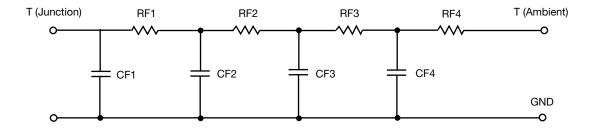
• n/a indicates not applicable

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

Revision: 18-Jul-11 Document Number: 63377

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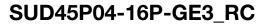
# **R-C THERMAL MODEL FOR FILTER CONFIGURATION**



THERMAL RESISTANCE (°C/W)					
Junction to	Ambient	Case	Foot		
RF1	N/A	1.2772	N/A		
RF2	N/A	1.0287	N/A		
RF3	N/A	444.3855m	N/A		
RF4	N/A	251.9742m	N/A		
	THERMAL CAPAC	ITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CF1	N/A	866.3629u	N/A		
CF2	N/A	10.0659m	N/A		
CF3	N/A	154.7390m	N/A		
CF4	N/A	1.9131	N/A		

## Note

• n/a indicates not applicable





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